Hema Chandra Prakash Movva

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Austin, TX 78758 USA

Research Fabrication and electrical transport measurements of layered semiconductor devices

EDUCATION The University of Texas at Austin, Austin, TX, USA Ongoing

Ph.D., Electrical and Computer Engineering, Advisors: Sanjay Banerjee, Emanuel Tutuc

The University of Texas at Austin, Austin, TX, USA May 2012

Phone: (512) 629-0181

M.S.E., Electrical and Computer Engineering, Advisor: Sanjay Banerjee

Indian Institute of Technology Bombay, Mumbai, India May 2009

B.Tech., Electrical Engineering, Thesis Advisor: Arun Chandorkar

HONORS AND Best Paper Award, Device Research Conference 2016

AWARDS

Best Paper Award, Device Research Conference 2015

Best Poster Award, Device Research Conference 2015

Best Poster Award, International Nanotechnology Conference (INC9) 2013

Silver Medal at the 37^{th} International Physics Olympiad 2005

National Talent Search (NTSE) scholarship 2003

Kishore Vaigyanik Protsahan Yojana (KVPY) fellowship 2003-05

SELECTED PUBLICATIONS

HCP Movva, B Fallahazad, K Kim, S Larentis, T Taniguchi, K Watanabe, SK Banerjee, E Tutuc Density-Dependent Quantum Hall States and Zeeman Splitting in Monolayer and Bilayer WSe₂, Phys. Rev. Lett., 118, 247701 (2017)

A Roy, <u>HCP Movva</u>, B Satpati, K Kim, R Dey, A Rai, T Pramanik, S Guchhait, E Tutuc, SK Banerjee, Structural and Electrical Properties of MoTe₂ and MoSe₂ Grown by Molecular Beam Epitaxy, ACS Appl. Mater. Interfaces, 8, 7396 (2016)

B Fallahazad, <u>HCP Movva</u>, K Kim, S Larentis, T Taniguchi, K Watanabe, SK Banerjee, E Tutuc Shubnikov—de Haas Oscillations of High-Mobility Holes in Monolayer and Bilayer WSe₂: Landau Level Degeneracy, Effective Mass, and Negative Compressibility, *Phys. Rev. Lett.*, **116**, 086601 (2016)

JH Park, <u>HCP Movva</u>, E Chagarov, K Sardashti, H Chou, I Kwak, KT Hu, SF Shirey, P Choudhury, SK Banerjee, AC Kummel, *In Situ* Observation of Initial Stage in Dielectric Growth, and Deposition of Ultrahigh Nucleation Density Dielectric on Two-Dimensional Surfaces, *Nano Lett.*, **15**, 6626 (2015)

<u>HCP Movva</u>, A Rai, S Kang, K Kim, B Fallahazad, T Taniguchi, K Watanabe, E Tutuc, SK Banerjee, **High-Mobility Holes in Dual-Gated WSe₂ Field-Effect Transistors**, ACS Nano, **9**, 10402 (2015)

<u>HCP Movva</u>, M Ramón, C Corbet, S Sonde, F Chowdhury, G Carpenter, E Tutuc, SK Banerjee, Self-aligned graphene field-effect transistors with polyethyleneimine doped source/drain access regions, *Appl. Phys. Lett.* **101**, *183113* (2012)

Full list at https://scholar.google.com/citations?user=c_IscTQAAAAJ&hl=en

Conference Presentations <u>HCP Movva</u>, B Fallahazad, K Kim, S Larentis, T Taniguchi, K Watanabe, SK Banerjee, E Tutuc, Carrier Density Dependent Quantum Hall States Sequence of Holes in WSe₂, APS March Meeting 2017

<u>HCP Movva</u>, S Kang, A Rai, K Kim, B Fallahazad, T Taniguchi, K Watanabe, E Tutuc, SK Banerjee, Room Temperature Gate-tunable Negative Differential Resistance in MoS₂/hBN/WSe₂ Heterostructures, 74th Device Research Conference 2016

HCP Movva, A Rai, S Kang, K Kim, S Guchhait, T Taniguchi, K Watanabe, E Tutuc, SK Banerjee, Top-gated WSe₂ field-effect transistors with Pt contacts, 73rd Device Research Conference 2015

HCP Movva, S Kang, A Rai, SK Banerjee, Ambipolar conduction in MoS₂/WSe₂ heterobilayers, APS March Meeting 2015

HCP Movva, P Jadaun, LF Register, SK Banerjee, Intercalated Bilayer Graphene Heterostructures towards the BiSFET, INC9 2013

<u>HCP Movva</u>, M Ramón, C Corbet, F Chowdhury, G Carpenter, E Tutuc, SK Banerjee, **Graphene** field-effect transistors with self-aligned spin-on-doping of source/drain access regions, 70th Device Research Conference 2012

RESEARCH PROJECTS

Transition metal dichalcogenide heterostructures and FETs

Jan 2014 - Present

Advisors: Sanjay Banerjee and Emanuel Tutuc Ph.D. research, UT Austin Currently involved in fabricating heterostructures and FETs using atomically thin transition metal dichalcogenides for exploring tunneling, and many-body phenomena via transport measurements.

Intercalated graphene heterostructures

Aug 2012 - Sep 2013

Advisor: Sanjay Banerjee

Ph.D. research, UT Austin

Fabricated, and characterized intercalated bilayer graphene heterostructures using Raman spectroscopy, X-ray diffraction, and temperature dependent transport measurements.

Surface-transfer doping of graphene

Jan 2011 - Feb 2012

Advisor: Sanjay Banerjee

M.S.E. Thesis, UT Austin

Developed a novel scheme of fabricating graphene field effect transistors (GFETs) with self-aligned gates and chemically doped source/drain access regions, resulting in improved device performance.

Work Experience

Solar Semiconductor Inc., Hyderabad, India

EXPERIENCE Engineer $R \mathcal{E}D$

Jun 2009 - Aug 2010

Worked on modelling the wattage loss incurred in c-Si PV module manufacturing processes. Developed distributed circuit models for c-Si PV modules. Worked on characterization of sun-simulators.

Texas Instruments, Bangalore, India

Circuit Design Intern

May 2008 - Aug 2008

Designed a high-speed dynamic latch based voltage comparator and devised a new characterization scheme for noise immunity. Built a 250 MSPS 6-bit SAR ADC using this comparator at its core.

SKILLS

Device fabrication: E-beam lithography, standard cleanroom processing

Device characterization: Probe stations, parameter analyzers, lock-in amps, He cryostats

Programming languages: Matlab/Scilab, LabVIEW, C/C++

ORGANIZATIONAL ACTIVITIES

President: Japan Karate Association of Austin

2013 - 2015

Co-ordinator: Techfest, IIT Bombay

2007

Organizer: Aagomani, Department of Electrical Engineering, IIT Bombay

2006